

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

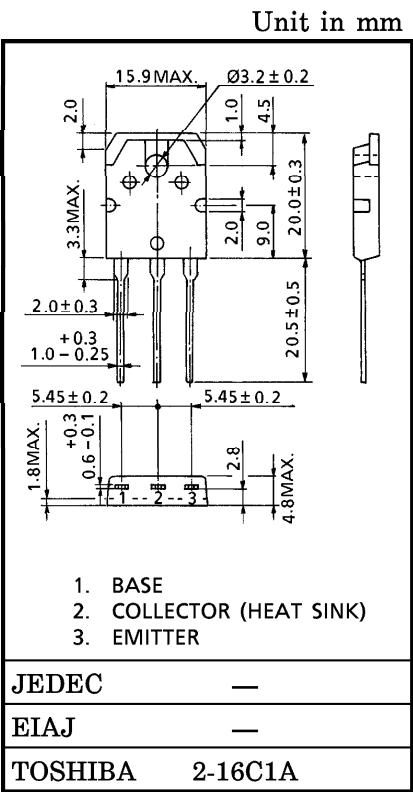
2SC5352

SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS
HIGH SPEED DC-DC CONVERTER APPLICATIONS

- Excellent Switching Times
: $t_r = 0.5 \mu s$ (Max.), $t_f = 0.3 \mu s$ (Max.) ($I_C = 4 A$)
- High Collectors Breakdown Voltage : $V_{CEO} = 400 V$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	10	A
	Pulse	I_{CP}	15	
Base Current		I_B	5	A
Collector Power Dissipation (Tc = 25°C)		P_C	80	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

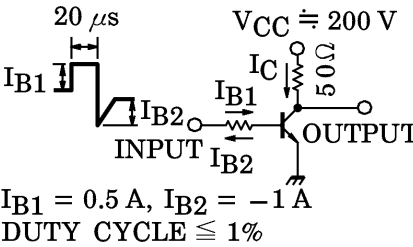


Weight : 4.7 g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 480 V, I _E = 0	—	—	100	μA
Emitter Cut-off Current		IEBO	V _{EB} = 7 V, I _C = 0	—	—	1	mA
Collector-Base Breakdown Voltage		V _(BR) CBO	I _C = 1 mA, I _E = 0	600	—	—	V
Collector-Emitter Breakdown Voltage		V _(BR) CEO	I _C = 10 mA, I _B = 0	400	—	—	V
DC Current Gain		h _{FE}	V _{CE} = 5 V, I _C = 1 A	20	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 4 A, I _B = 0.5 A	—	—	1.0	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C = 4 A, I _B = 0.5 A	—	—	1.3	V
Switching Time	Rise Time	t _r	 V_{CC} = 200 V I_C R_L INPUT OUTPUT I_{B1} = 0.5 A, I_{B2} = -1 A DUTY CYCLE ≤ 1%	—	—	0.5	μs
	Storage Time	t _{stg}		—	—	2.0	
	Fall Time	t _f		—	—	0.3	

